



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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N-Channel Power MOSFET

30V, 5.5A, 32mΩ

FEATURES

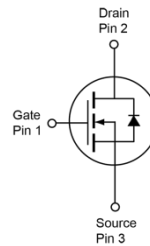
- Low $R_{DS(on)}$ to minimize conductive losses
- Low gate charge for fast power switching
- Compliant to RoHS directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

KEY PERFORMANCE PARAMETERS

PARAMETER		VALUE	UNIT
V_{DS}		30	V
$R_{DS(on)}$ (max)	$V_{GS} = 4.5V$	32	mΩ
	$V_{GS} = 2.5V$	40	
Q_g		8.9	nC

APPLICATIONS

- Battery Power Management
- ORing FET/Load Switch


SOT-23


Note: MSL 3 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 12	V
Continuous Drain Current (Note 1)	$T_C = 25^\circ\text{C}$	I_D	5.5	A
	$T_A = 25^\circ\text{C}$		4	
Pulsed Drain Current		I_{DM}	22	A
Total Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	1.8	W
	$T_C = 125^\circ\text{C}$		0.4	
Total Power Dissipation	$T_A = 25^\circ\text{C}$	P_D	1	W
	$T_A = 125^\circ\text{C}$		0.2	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	- 55 to +150	$^\circ\text{C}$

THERMAL PERFORMANCE

PARAMETER	SYMBOL	LIMIT	UNIT
Junction to Case Thermal Resistance	$R_{\theta JC}$	70	$^\circ\text{C/W}$
Junction to Ambient Thermal Resistance	$R_{\theta JA}$	124	$^\circ\text{C/W}$

Thermal Performance Note: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins. $R_{\theta JA}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.

ELECTRICAL SPECIFICATIONS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static						
Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	BV _{DSS}	30	--	--	V
Gate Threshold Voltage	V _{GS} = V _{DS} , I _D = 250μA	V _{GS(TH)}	0.4	0.75	0.9	V
Gate-Source Leakage Current	V _{GS} = ±12V, V _{DS} = 0V	I _{GSS}	--	--	±100	nA
Drain-Source Leakage Current	V _{GS} = 0V, V _{DS} = 30V	I _{DSS}	--	--	1	μA
	V _{GS} = 0V, V _{DS} = 30V T _J = 125°C		--	--	100	
	Drain-Source On-State Resistance (Note 2)		V _{GS} = 4.5V, I _D = 4A	R _{DS(on)}	--	
	V _{GS} = 2.5V, I _D = 4A	--	32		40	
Forward Transconductance (Note 2)	V _{DS} = 5V, I _D = 4A	g _{fs}	--	9.5	--	S
Dynamic (Note 3)						
Total Gate Charge	V _{GS} = 4.5V, V _{DS} = 15V, I _D = 4A	Q _g	--	8.9	--	nC
Total Gate Charge	V _{GS} = 2.5V, V _{DS} = 15V, I _D = 4A	Q _g	--	5.1	--	
Gate-Source Charge		Q _{gs}	--	1.5	--	
Gate-Drain Charge		Q _{gd}	--	2	--	
Input Capacitance	V _{GS} = 0V, V _{DS} = 15V f = 1.0MHz	C _{iss}	--	792	--	pF
Output Capacitance		C _{oss}	--	53	--	
Reverse Transfer Capacitance		C _{rss}	--	21	--	
Gate Resistance	f = 1.0MHz, open drain	R _g	--	1	--	Ω
Switching (Note 3)						
Turn-On Delay Time	V _{GS} = 10V, V _{DS} = 15V, I _D = 4A, R _G = 2Ω,	t _{d(on)}	--	5.8	--	ns
Turn-On Rise Time		t _r	--	32	--	
Turn-Off Delay Time		t _{d(off)}	--	19	--	
Turn-Off Fall Time		t _f	--	28	--	
Source-Drain Diode						
Forward Voltage (Note 2)	V _{GS} = 0V, I _S = 4A	V _{SD}	--	--	1	V
Reverse Recovery Time	I _S = 4A , dI/dt = 100A/μs	t _{rr}	--	8	--	ns
Reverse Recovery Charge		Q _{rr}	--	3.3	--	nC

Notes:

1. Silicon limited current only.
2. Pulse test: Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
3. Switching time is essentially independent of operating temperature.

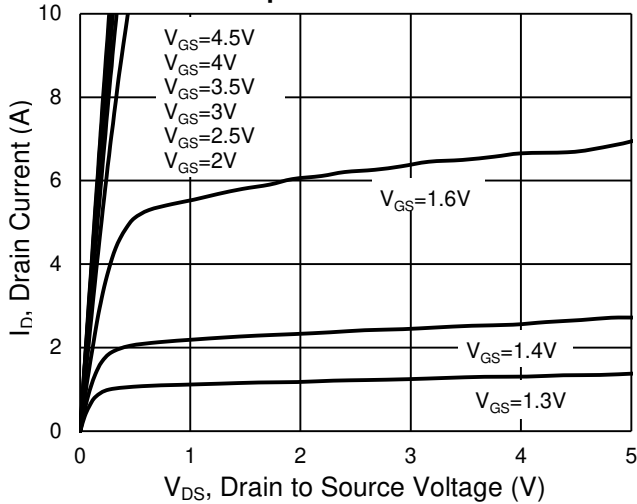
ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM320N03CX RFG	SOT-23	3,000pcs / 7" Reel

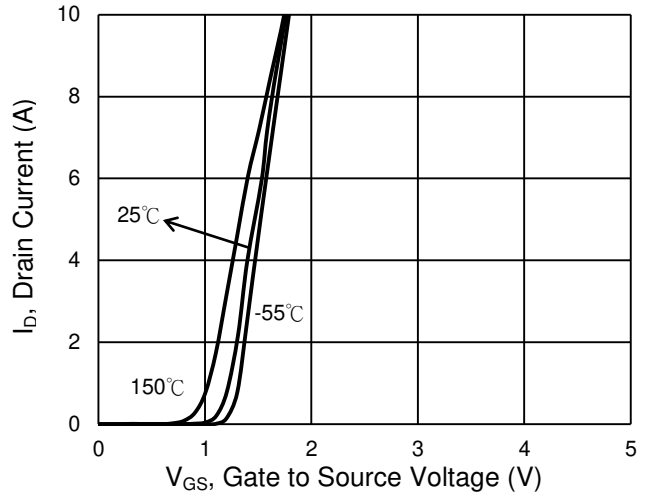
CHARACTERISTICS CURVES

($T_A = 25^\circ\text{C}$ unless otherwise noted)

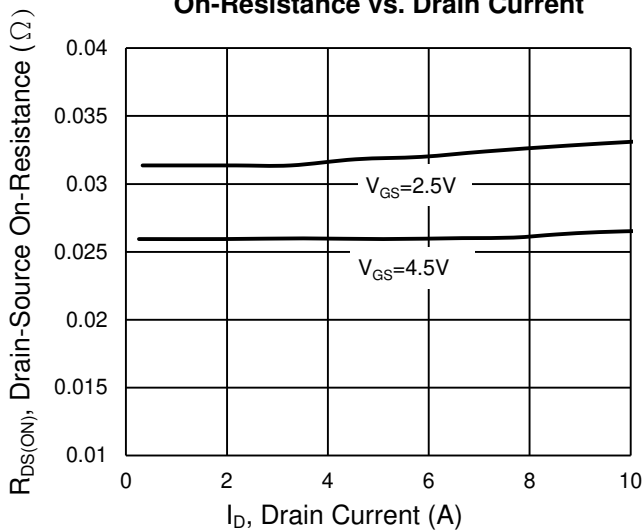
Output Characteristics



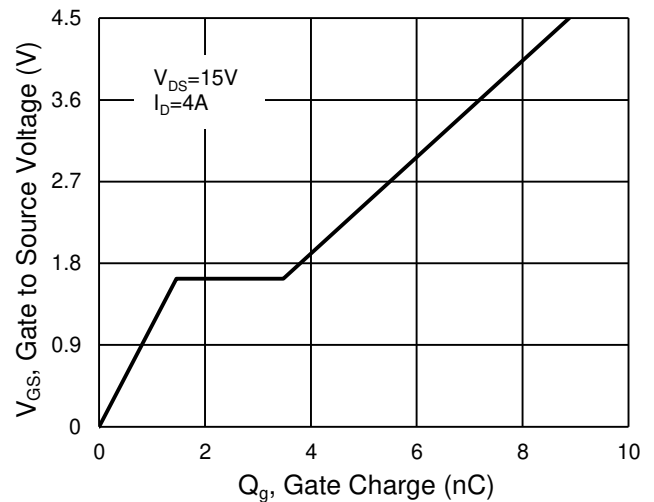
Transfer Characteristics



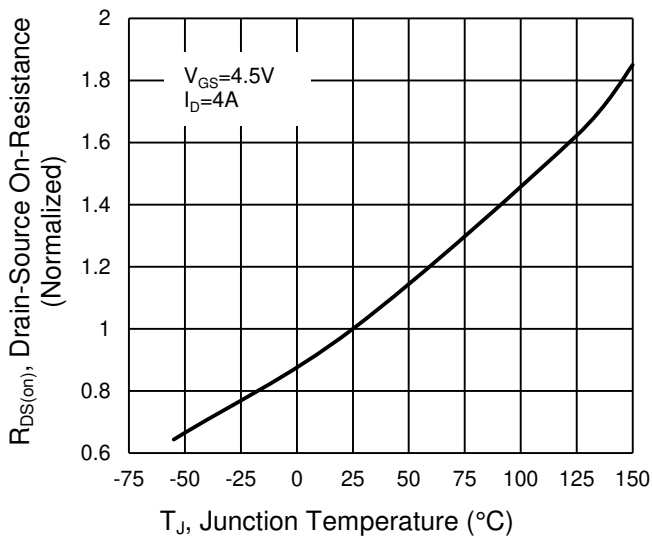
On-Resistance vs. Drain Current



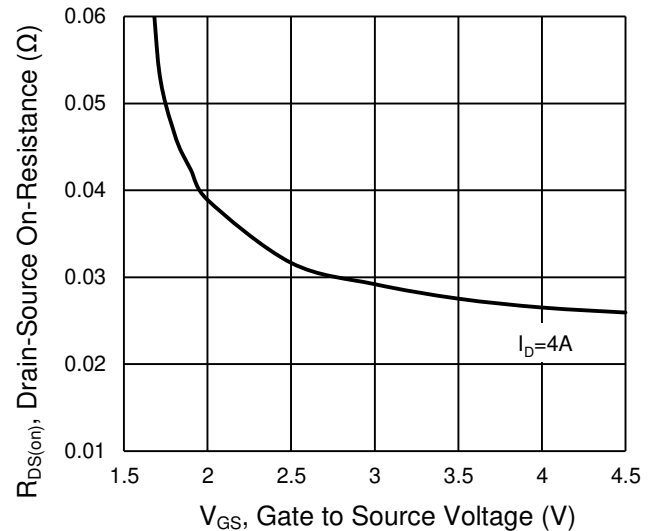
Gate-Source Voltage vs. Gate Charge



On-Resistance vs. Junction Temperature



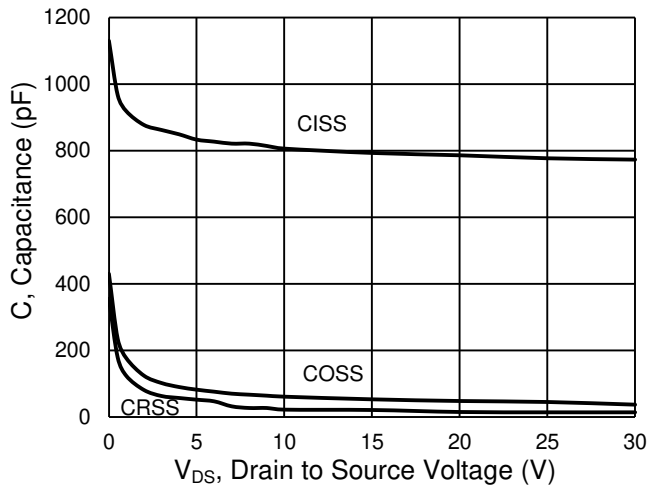
On-Resistance vs. Gate-Source Voltage



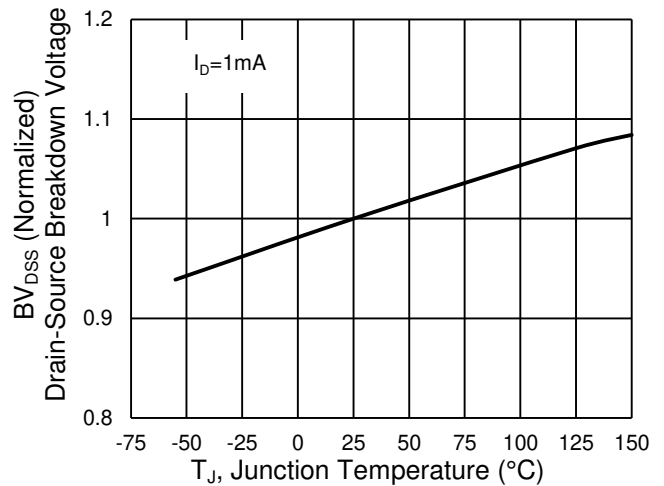
CHARACTERISTICS CURVES

($T_A = 25^\circ\text{C}$ unless otherwise noted)

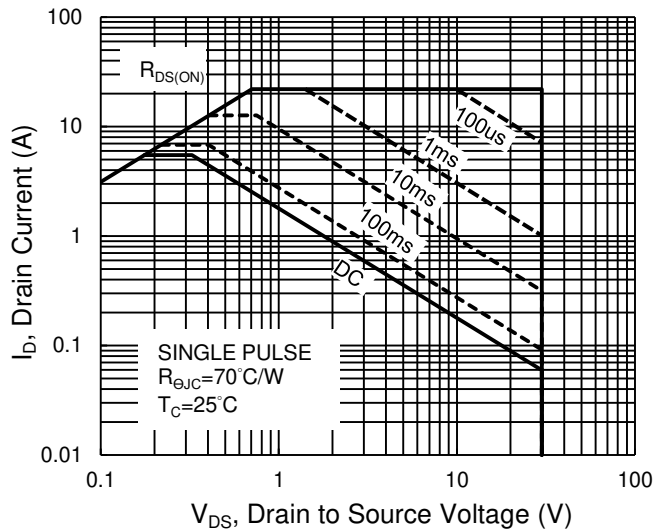
Capacitance vs. Drain-Source Voltage



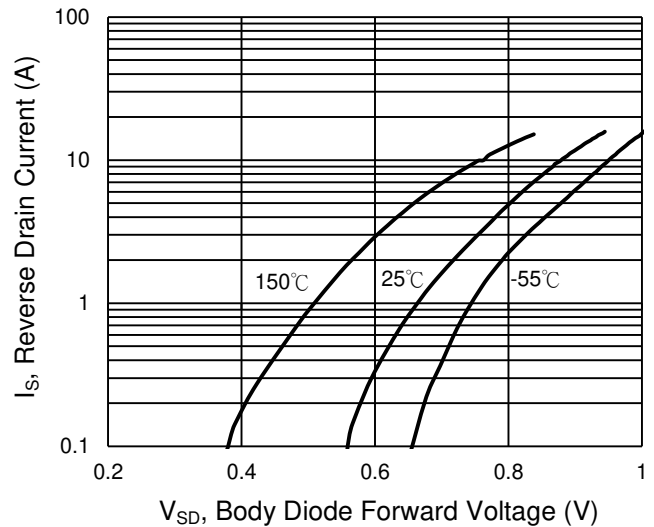
BV_{DSS} vs. Junction Temperature



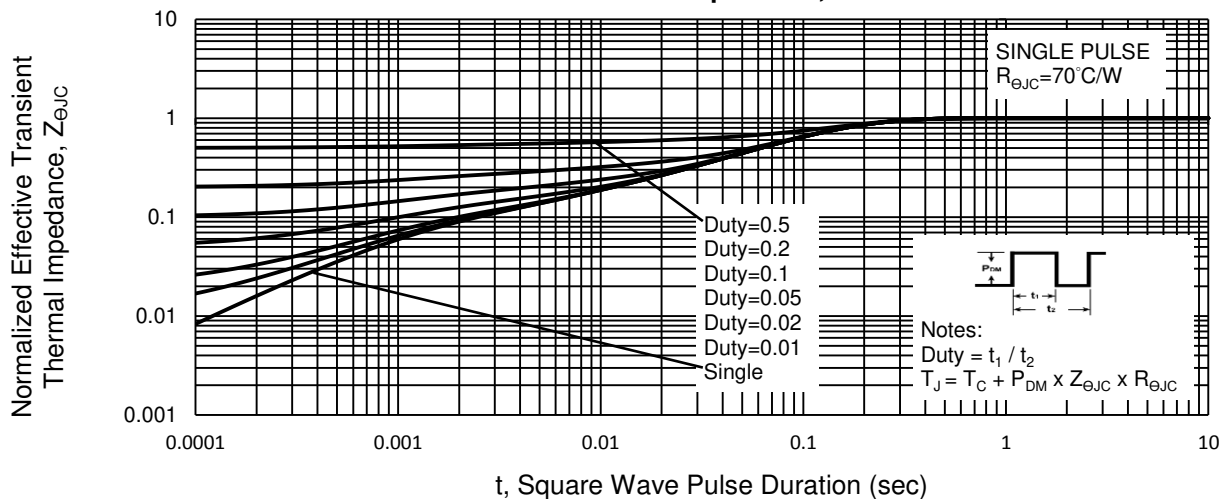
Maximum Safe Operating Area, Junction-to-Case



Source-Drain Diode Forward Current vs. Voltage

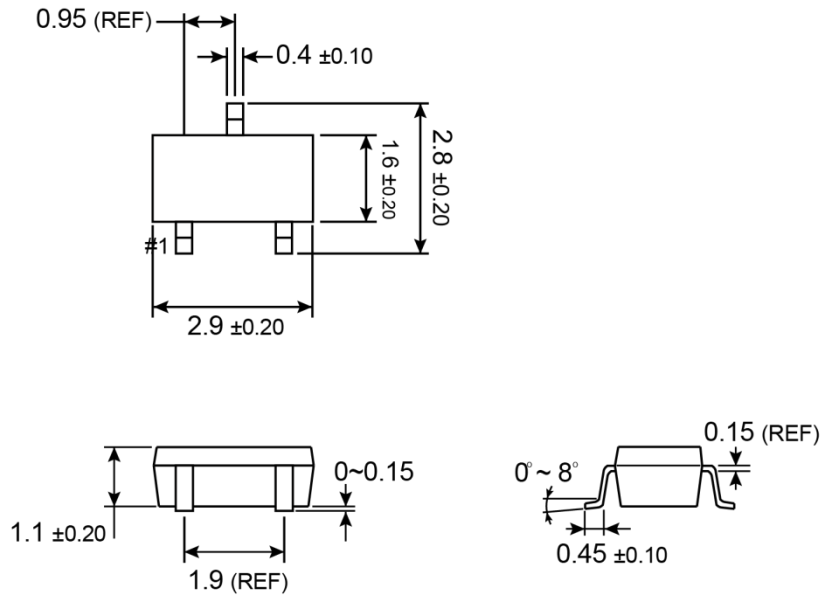


Normalized Thermal Transient Impedance, Junction-to-Case

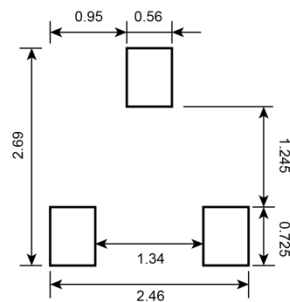


PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

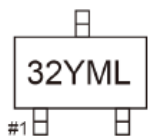
SOT-23



SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM



32 = Device Code

Y = Year Code

M = Month Code

O =Jan **P** =Feb **Q** =Mar **R** =Apr

S =May **T** =Jun **U** =Jul **V** =Aug

W =Sep **X** =Oct **Y** =Nov **Z** =Dec

L = Lot Code

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